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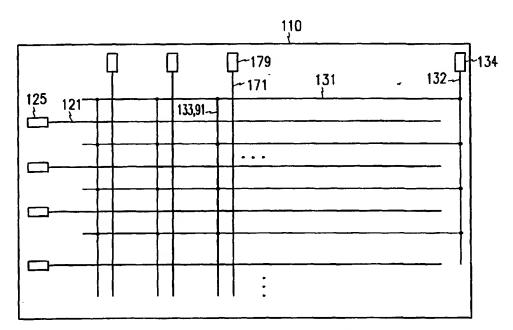
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(54) Title: THIN FILM TRANSISTOR ARRAY PANEL



(57) Abstract: A gate wire and a storage electrode wire extending in a transverse direction are provided, and a data wire extending in a longitudinal direction intersects the gate wire and the storage electrode wire. A plurality of pixel electrodes and a plurality of TFTs are provided on pixel areas defined by the intersections of the data wire and the gate wire. The storage electrode wire is interconnected by a plurality of storage electrodes connections provided on the pixel areas. In this way, a common bar disposed between gate pads and a display area is omitted or has reduced width. Therefore, the fan-out areas becomes to have sufficient size to reduce the resistance difference between the signal lines.

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